

# Towards the Final Telescope Sensor : TC/MIMOSA-26

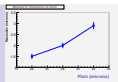
## Progress Report

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*on behalf of IPHC and IRFU/Saclay*

## OUTLINE

- Strategy of the chip development (reminder)
- Column parallel sensor prototyping : *Objectives of IDC prototyping – Lab & beam test results*
- The question of radiation tolerance
- SDC-2/SUZE-01 zero suppression  $\mu$ circuit : *Established performances*
- Final chip : status of design and plans
- Summary - Outlook

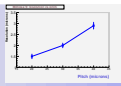


## ■ Motivation for a dedicated beam telescope architecture:

- ⇒ *beam intensity : read-out  $\lesssim 10^4$  frames / second*
- ⇒ *DUT surface & resolution requirements : active surface of  $1 \times 2 \text{ cm}^2$  with  $\gtrsim 0.5$  million pixels*
- ⇒ *sensor should incorporate zero suppression ⇒ + integrated signal discrimination*

## ■ Development strategy: *two prototyping lines pursued in parallel*

- ⇒ *column // architecture adapted to the required speed ▷ MIMOSA-16 ▷ **IDC/MIMOSA-22***
- ⇒ *integrated  $\emptyset$  & output memories adapted to the corresponding occupancy ▷ **SDC-2 /SUZE-01***



## ■ Specific goals of IDC :

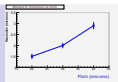
- ⇨ *validate the fast read-out architecture developed in MIMOSA-16 (next slide ) at **Real Scale***
- ⇨ *extract an optimal pixel design (sensing diode and signal processing  $\mu$ circuits)*
- ⇨ *improve the chip testability (JTAG, analog outputs, pads, ...)*

## ■ 2 versions of IDC designed and fabricated :

- ⇨ *MIMOSA-22 : mainly for overall pixel architecture definition*
- ⇨ *MIMOSA-22bis : robustness, fine tuned optimisation, radiation tolerance*

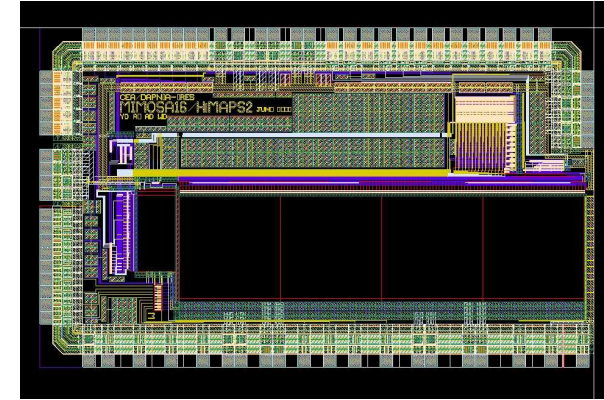
## ■ Objective beyond IDC :

- ⇨ *once validated, the IDC architecture will be merged with SDC-2*
  - ⇒ *Final Sensor (TC/MIMOSA-26), to be sent for fabrication in Novembre*



# Performances of a Small Prototype with Digitised Output

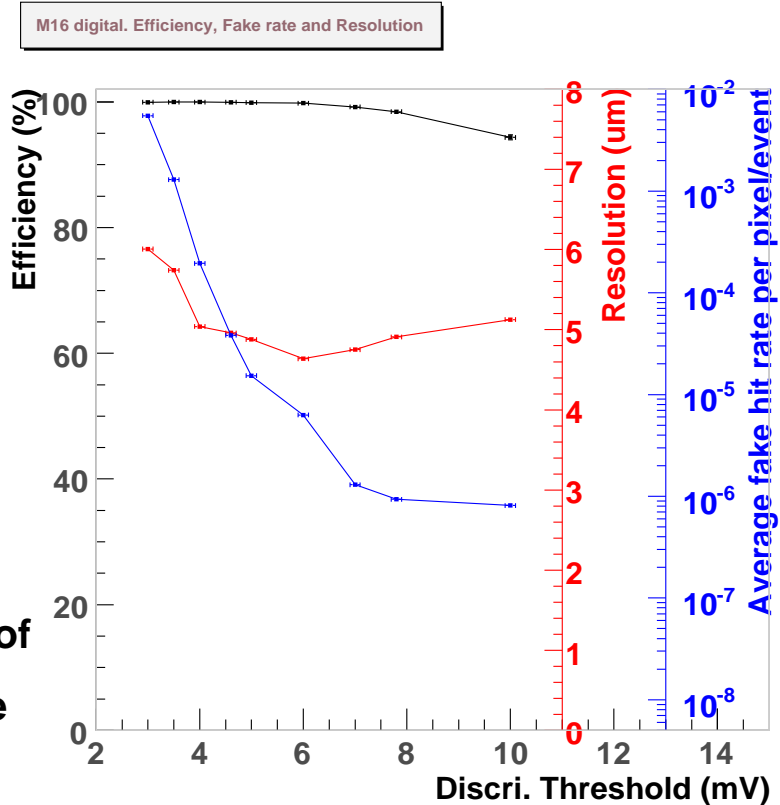
- MIMOSA-16 :
  - ◇ fabricated in 2006 (coll. with IRFU/Saclay)
  - ◇ 32 col. of 128 pixels (25  $\mu m$  pitch, integrated CDS )
  - ◇ 24 col. ended with an integrated discriminator
  - ◇ 4 different pixels (i.e. 4 sub-arrays)



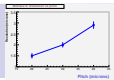
- Tests at CERN-SPS ( $\sim 180 \text{ GeV } \pi^-$ ) in Summer 2007
  - results of one sub-array (S4)



Discri. threshold	Detection eff.	Fake rate	Resolution
4 mV	$99.96 \pm 0.03 \text{ (stat) } \%$	$\sim 2 \cdot 10^{-4}$	$\sim 4.8 - 5.0 \mu m$
6 mV	$99.88 \pm 0.05 \text{ (stat) } \%$	$< 10^{-5}$	$\sim 4.6 \mu m$



▷▷▷ Architectures of pixel (integrated CDS ) and of full chain made of "columns ended with integrated discri." validated at small scale



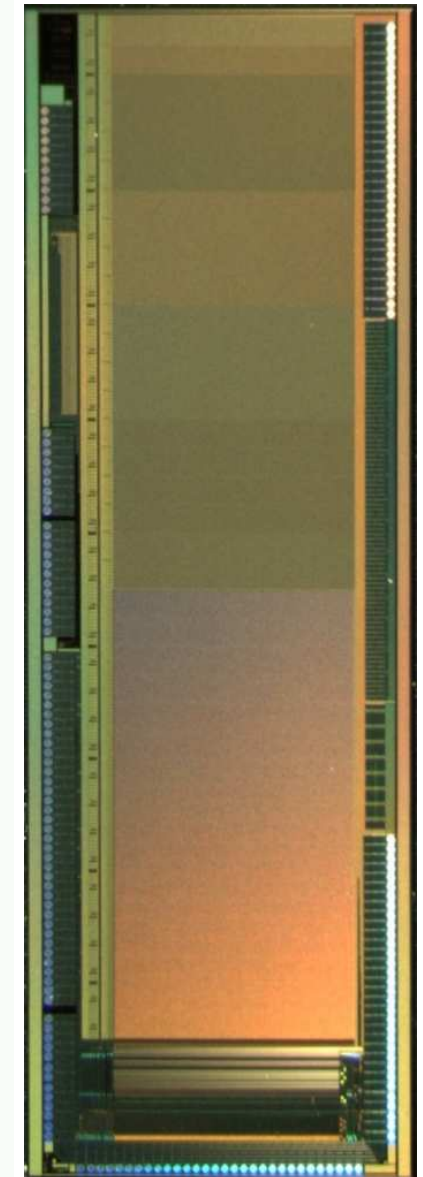
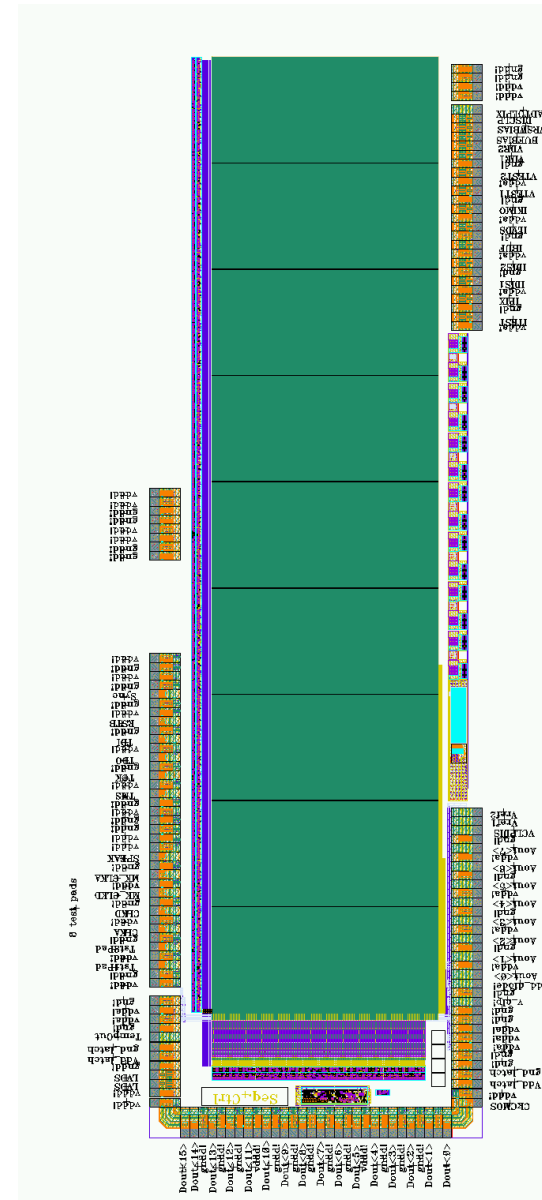
♣ Extension of MIMOSA-16  $\rightarrow$  larger surface, smaller pitch, optimised pixel, JTAG, more testability

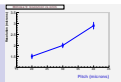
## Pixel characteristics (optimal charge coll. diode size ?) :

- ✳ pitch :  $18.4 \mu m$  (compromise resolution/pixel layout)
- ✳ diode surface :  $\sim 10 - 20 \mu m^2$  to optimise charge coll. & gain
- ✳ 128 columns ended with discriminator
- ✳ 576 pixels per column ( $\equiv$  final column length)
- ✳ 8 columns with analog output for test purposes
- ✳ 9 sub-matrices of 64 rows :
  - 17 pixel designs w/o ionising rad. tol. diode
  - $\Rightarrow$  active digital area  $\sim 25 mm^2$  (128 x 576 pixels)
- ✳ read-out time  $\sim 100 \mu s$  ( $\sim 10^4$  frames/s)

## Testability :

- ✳ JTAG + bias DAC  $\rightarrow$  programmable chip steering
- ✳ 2 additional DC voltages to emulate pixel's output for independent discriminator performance assessment
- ✳ output frequency  $\leq 40$  MHz





## ■ Topics investigated :

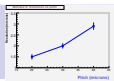
- ✧ *optimum between CCE ( $\Rightarrow$  large diode) and capacitive noise ( $\Rightarrow$  small diode)*
- ✧ *effective and robust pre-amplification scheme*
- ✧ *low noise (ionising) radiation tolerant design*
- ✧ *temperature dependence of performances*
- ✧ *performance uniformity over full active surface*
- ✧ *comparison with MIMOSA-16 performances (24 columns of 128 pixels)*

## ■ 5 pixel designs implemented, combining 2 reset & 2 ampli. variants (w/o rad. tol. diode, diff. diode sizes):

- ✧ *reset diode with (standard) common source amplifier : w/o improved gain*
- ✧ *self-biased feedback diode with common source amplifier with improved gain*
- ✧ *feedback reset diode with common source amplifier : w/o improved gain*

## ■ Status :

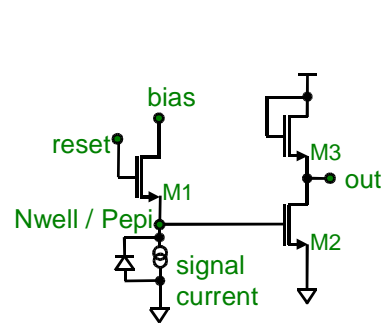
- ✧ *back from foundry since Feb.'08*
- ▷ *lab tests of analog and digital (discr.) outputs with  $^{55}\text{Fe}$  source completed*
- ▷ *first beam tests (CERN-SPS / August '08) analysed*



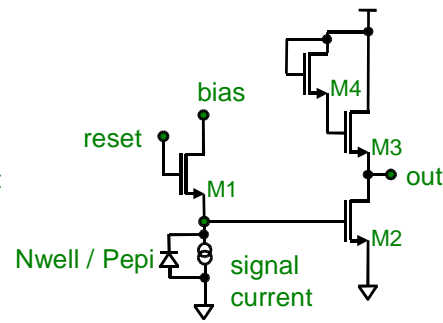
## Various pixel designs (rad. tol. and standard) :

✧ *reset diode (improved gain)*

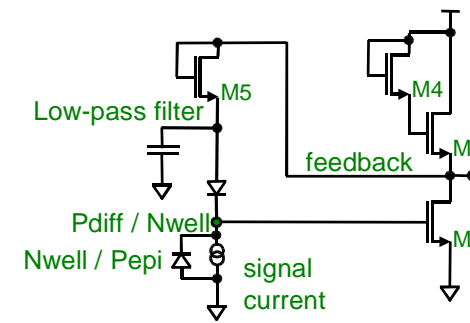
✧ *self-biased diode with feedback (improved gain)*



(S13)



(S10)



(S6)

## Main results obtained with exposure to $^{55}\text{Fe}$ source ( $t_{r.o.} = 92.5 \mu\text{s}$ ) :

✧ *Noise :*

≈ *Temporal (pixel) Noise*  $\sim 0.5 - 0.7 \text{ mV}$  ( $10 < N < 14 e^- \text{ ENC}$ )

≈ *FPN*  $\sim 0.25 \text{ mV}$

≈ *N (rad. tol. pixels)*  $\sim N$  (*standard pixels*)  $+ 1 e^- \text{ ENC}$

✧ *Cluster CCE :*

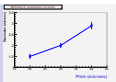
≈ *3x3 pixels* : 70 – 80 %

≈ *5x5 pixels* : 80 – 90 %

✧ *modest T dependence between*  $\sim 10^\circ \text{C}$  *and*  $35^\circ \text{C}$  :  $\lesssim 10\%$  *noise variation*

✧ *5 different chips characterised : identical performances within*  $\pm 5\%$

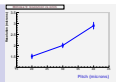




	S6		S7		S8		S9		S10	
	mV	e-	mV	e-	mV	e-	mV	e-	mV	e-
TN	0.612	11.5	0.601	10.7	0.615	11.3	0.595	10.0	0.639	11.6
FPN	0.250	4.7	0.263	4.6	0.254	4.4	0.273	4.6	0.222	4.0
	S12		S13		S15		S16		S17	
	mV	e-	mV	e-	mV	e-	mV	e-	mV	e-
TN	0.636	11.2	0.692	13.4	0.682	12.8	0.536	12.4	0.527	11.4
FPN	0.225	4.0	0.269	5.2	0.277	5.2	0.218	5.1	0.217	4.7

- Pixel Noise ~ 0.6mV
  - FPN ~ 0.25 mV
  - RadTol pixels (S6, S10, S13) Noise slightly higher than for standard pixels
- ⇒ Similar results than smaller prototype MIMOSA16 ones





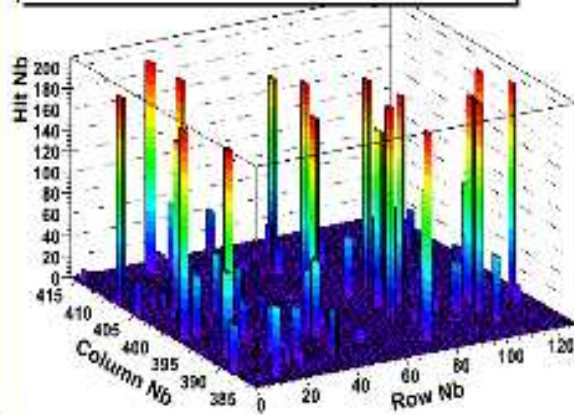
S12 response for 3, 5 and 7 mV threshold without and with  $^{55}\text{Fe}$  source

3 mV threshold

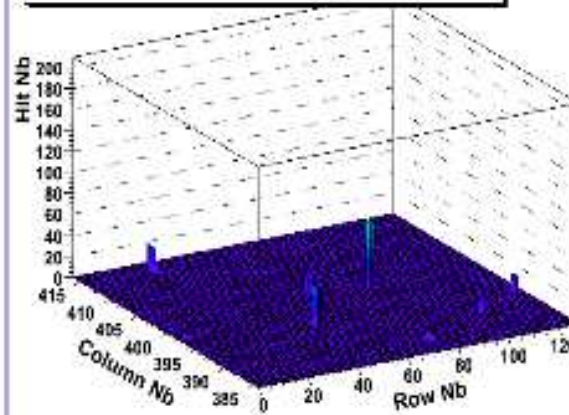
5 mV threshold

7 mV threshold

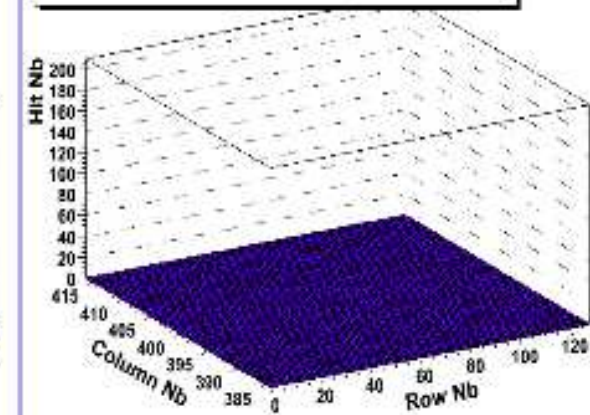
Discri + Pixels without source ; 3 mV Threshold



Discri + Pixels without source ; 5 mV Threshold

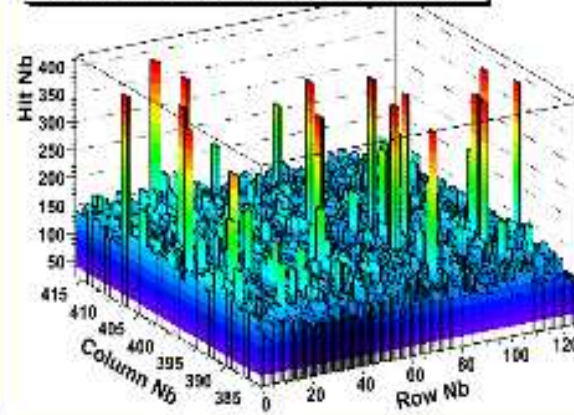


Discri + Pixels without source ; 7 mV Threshold



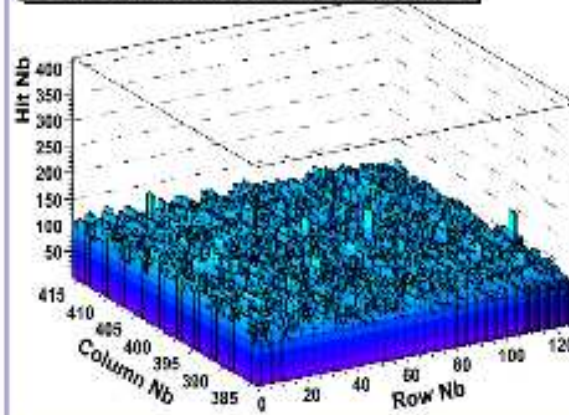
Without source

Discri + Pixels with source ; 3 mV Threshold



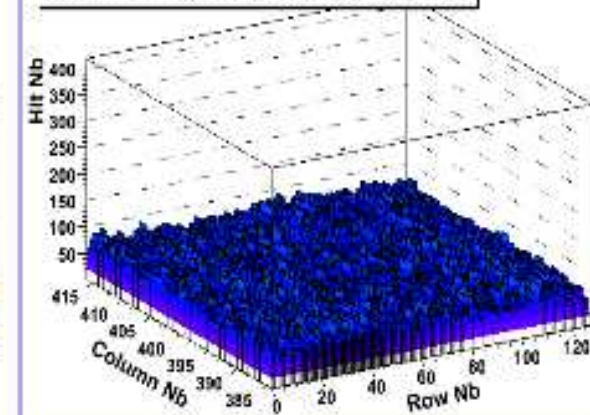
100.000 events

Discri + Pixels with source ; 5 mV Threshold



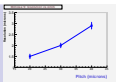
100.000 events

Discri + Pixels with source ; 7 mV Threshold

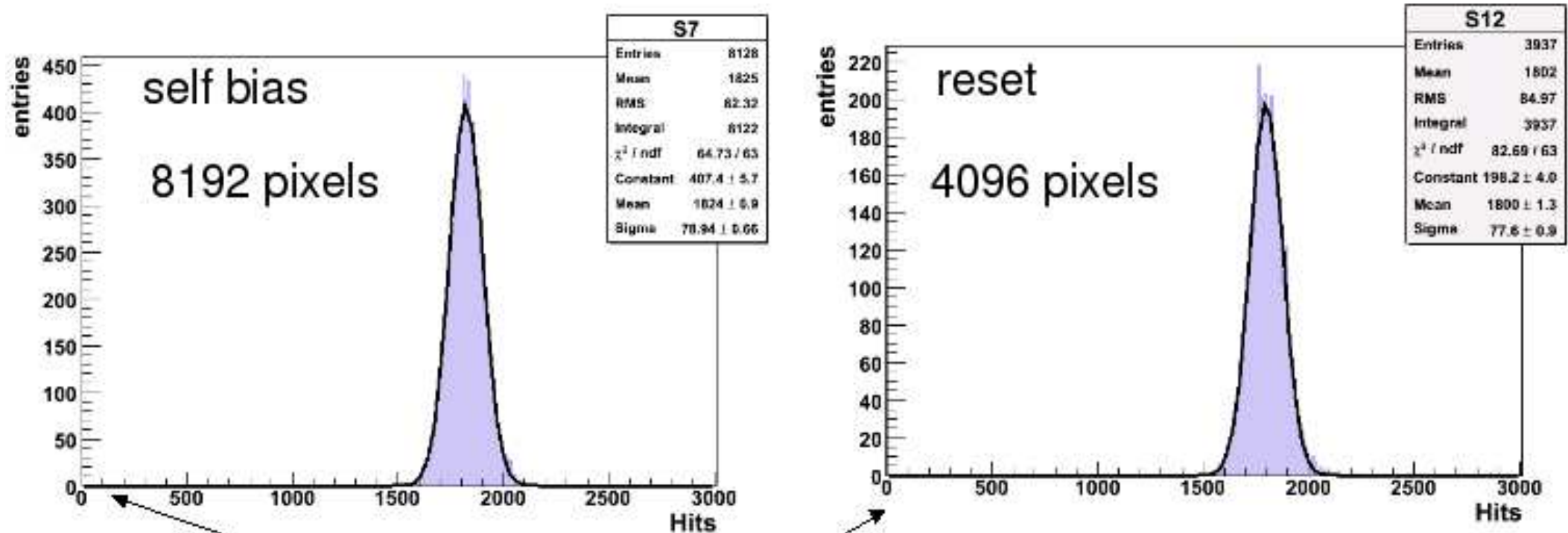


100.000 events

With source



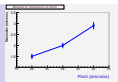
5 mV threshold with  $^{55}\text{Fe}$  source



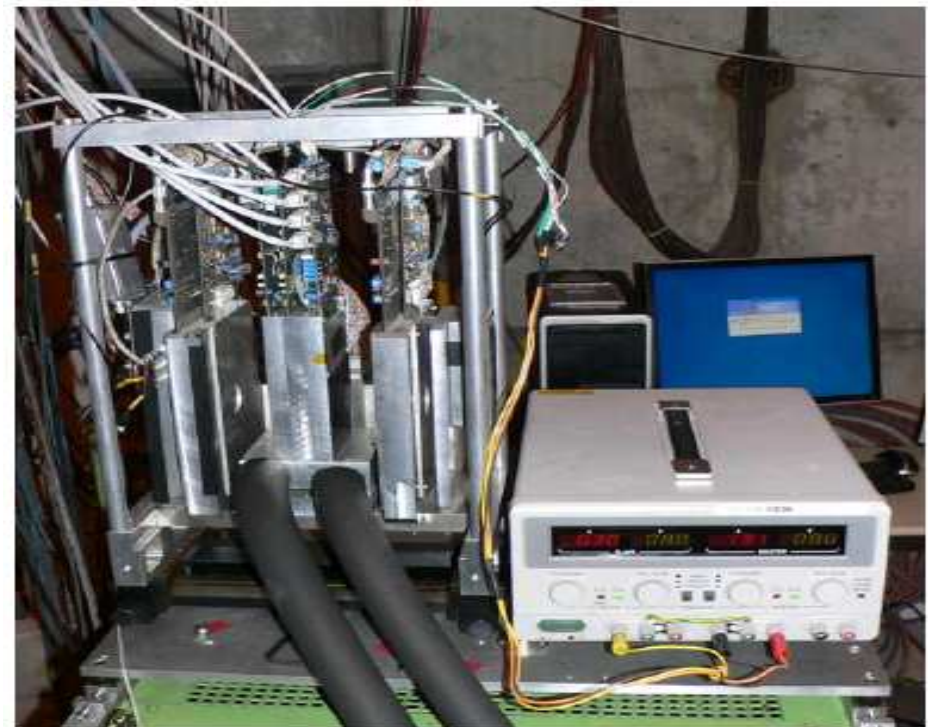
No dead pixel number

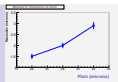
Good uniformity of discriminator response, within 4%



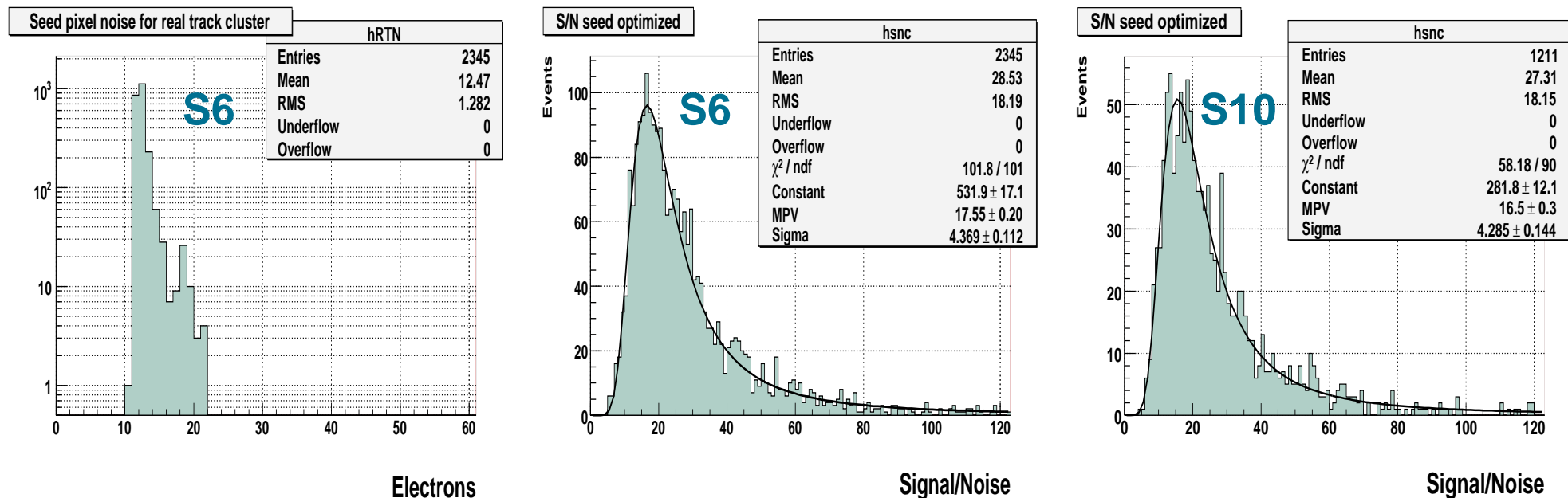


- **4 weeks of beam time at CERN-SPS :**
  - ▷ *~ 2 weeks in August with MIMOSA-22 (EUDET period)*
  - ▷ *~ 2 weeks in Sept.-Oct. with MIMOSA-22bis (SiLC period)*
  
- **T4-H6 beam line :  $\sim 120 \text{ GeV } \pi^-$  beam** ▷▷▷▷
  
- **Chips mounted at center of Si-strip telescope**  
*(4 pairs of orthogonal strips)* ▷▷▷▷
  
- **2 MIMOSA-22 and 4 MIMOSA-22bis chips tested**  
*at several values of discriminator threshold*
  
- **> 1 million tracks reconstructed in the sensors**





## Noise and S/N (seed pixel ) distributions delivered by the 8 columns without discriminator

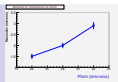


## Detection performances (det. eff. , N and S/N for hits where the seed pixel exhibits $S/N > 4$ ) :

Sub-array	S6	S7	S8	S9	S10	S12	S13
Det. eff.	99.93 % $\pm 0.05$ %	99.95 % $\pm 0.04$ %	100.00 % +0/-0.30 %	100.00 % +0/-0.14 %	99.87 % $\pm 0.09$ %	100.00 % +0/-0.08 %	100.00 % +0/-0.07 %
N ( $e^-$ ENC)	$12.5 \pm 0.1$	$11.6 \pm 0.1$	$12.3 \pm 0.1$	$10.6 \pm 0.1$	$13.6 \pm 0.1$	$12.1 \pm 0.1$	$14.0 \pm 0.1$
S/N (seed, MPV)	$17.6 \pm 0.2$	$18.5 \pm 0.2$	$20.9 \pm 1.1$	$19.5 \pm 0.5$	$16.5 \pm 0.3$	$18.2 \pm 0.3$	$16.0 \pm 0.3$

✳ very satisfactory performances ( det. eff.  $\sim 99.9$  % and single pt resolution  $\lesssim 1.5 \mu m$  )

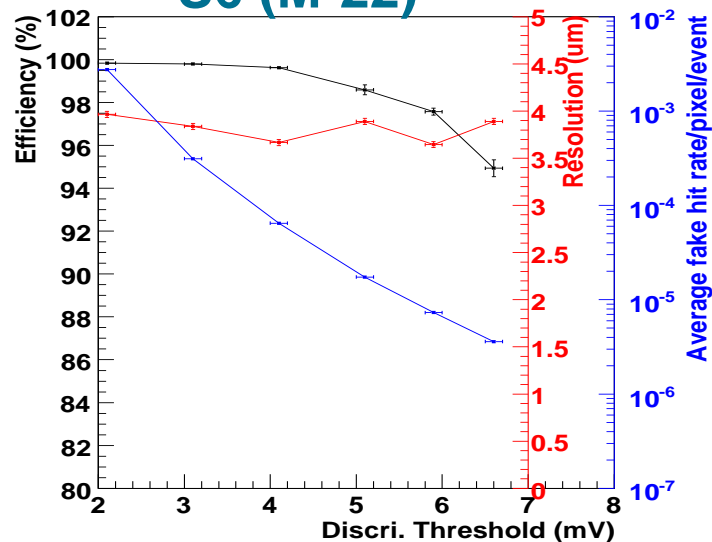
⇒ pixel architecture (diode size, rad. tol. diode design, amplification scheme ) validated



Det. eff., fake hit rate & spatial resolution for S6 & S10 (M-22) and S2 (M-22bis) vs discri. threshold :

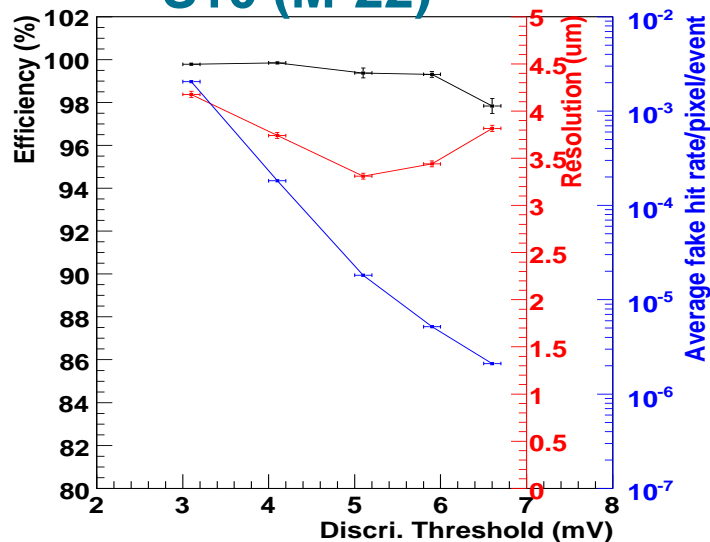
M22 digital S6. Efficiency, Fake rate and Resolution

S6 (M-22)



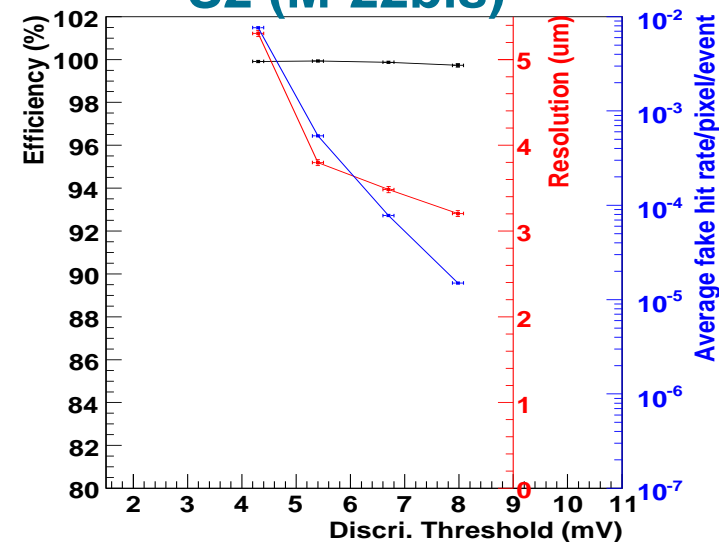
M22 digital S10. Efficiency, Fake rate and Resolution

S10 (M-22)



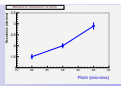
M22bis digital S2. Efficiency, Fake rate and Resolution

S2 (M-22bis)

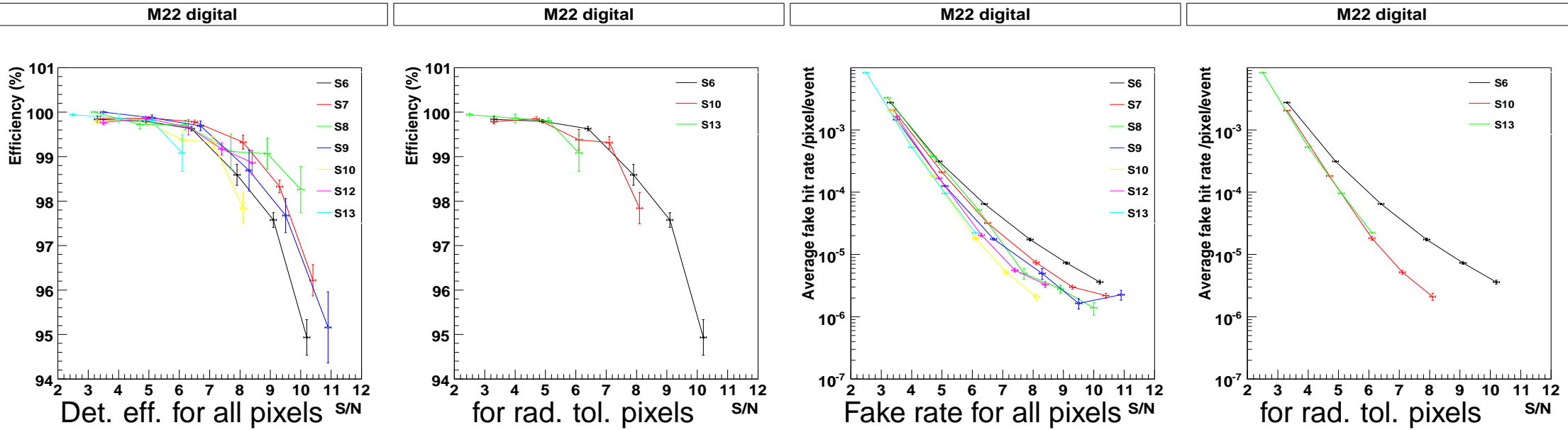


### Main results:

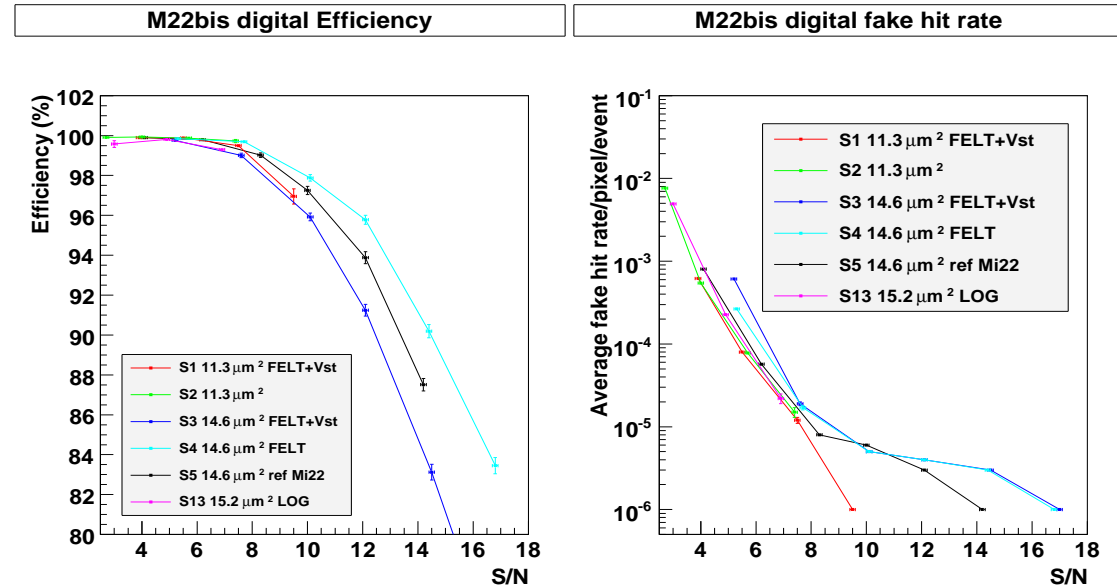
- \* rather marginal performance differences between  $> 10$  diff. pixels (e.g. rad. tol. vs standard)
- \* det. eff. of analog output  $\sim 99.9\%$  for all sub-arrays  $\Rightarrow$  pixel architecture validated
- \* det. eff. of digital output  $\gtrsim 99.8\%$  for almost all sub-arrays (agrees with MIMOSA-16)
- \* fake hit rate very low ( $O(10^{-4} - 10^{-5})$ ) while det. eff. still near 100%
- \* single point resolution  $\gtrsim 3.5 \mu\text{m}$  (as expected)
- \* no performance non-uniformity observed over the chip surface  $\Rightarrow$  real scale check validated

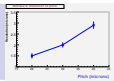


## Comparison of det. efficiency & fake hit rate vs S/N for all sub-arrays :



- ▷ Observed performance differences and analysis maturity don't allow yet to decide for the BT pixel architecture
- ▷ Radiation tolerance assessment needed to converge on most adequate pixel design





# The Question of Radiation Tolerance

## Why may radiation tolerance be a concern ?

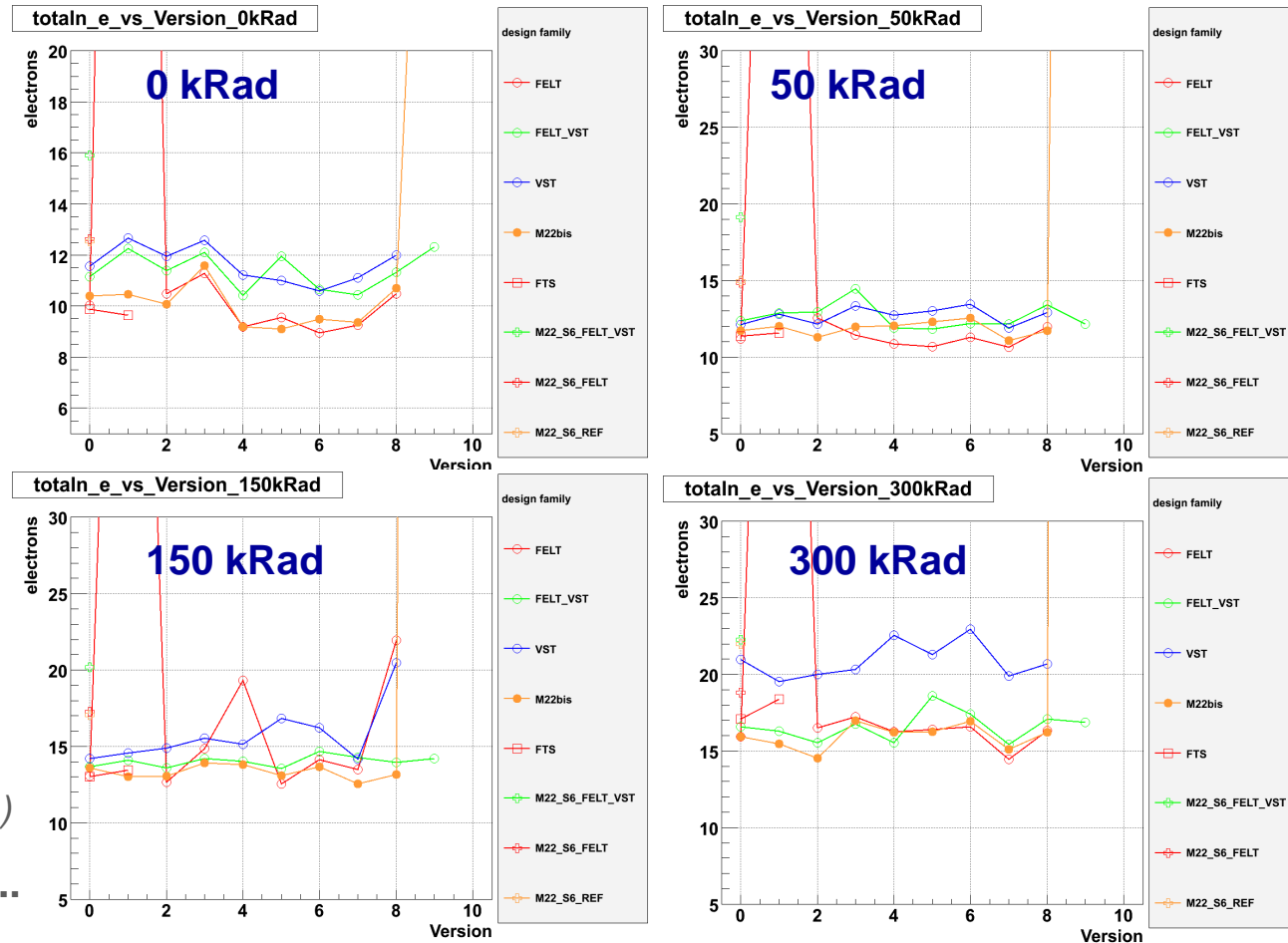
- \* max. annual doses at DESY  $\lesssim 10^{11} e^-$  (few GeV)/yr  $\Rightarrow \lesssim 3.5 \text{ kRad} \ \& \ 10^{10} n_{eq}/cm^2$
- \* max. annual doses at CERN  $\lesssim$  several  $10^{12} \pi^-$  ( $10^2 \text{ GeV}$ )/yr  $\Rightarrow \lesssim O(10^2) \text{ kRad} \ \& \ O(10^{12}) n_{eq}/cm^2$

## Assessing rad. tolerance (10 keV X-Rays) in lab.:

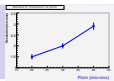
▷ ex. of S6 (M22) variants at 20° C

- \* before irradiation  $\gtrsim 9.5 e^- \text{ ENC}$
- \* after 50 kRad  $\gtrsim 11 e^- \text{ ENC}$
- \* after 150 kRad  $\gtrsim 13 e^- \text{ ENC}$
- \* after 300 kRad  $\gtrsim 15 e^- \text{ ENC}$

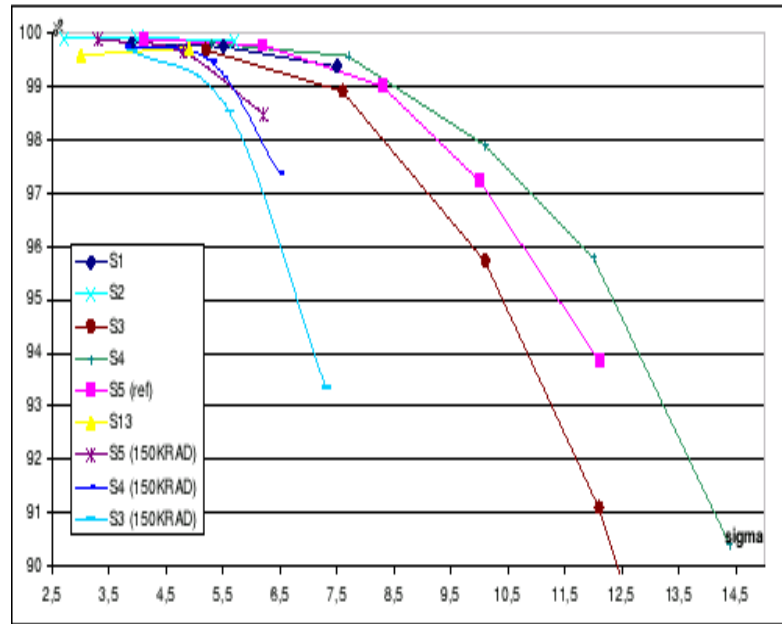
▷▷▷ **Excellent noise performance**  
 (but source of noise increase still under study)  
 ... watch Charge Collection Efficiency ...







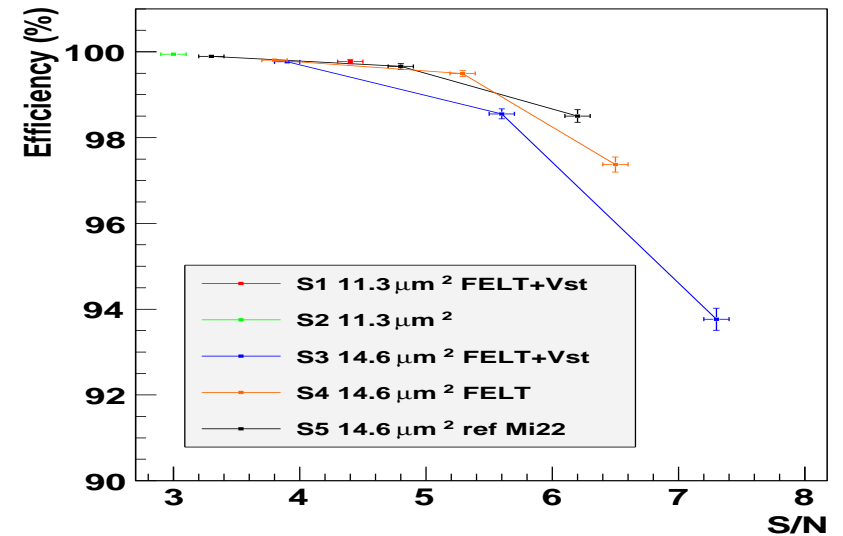
Beam test results with chips irradiated with 150 kRad :



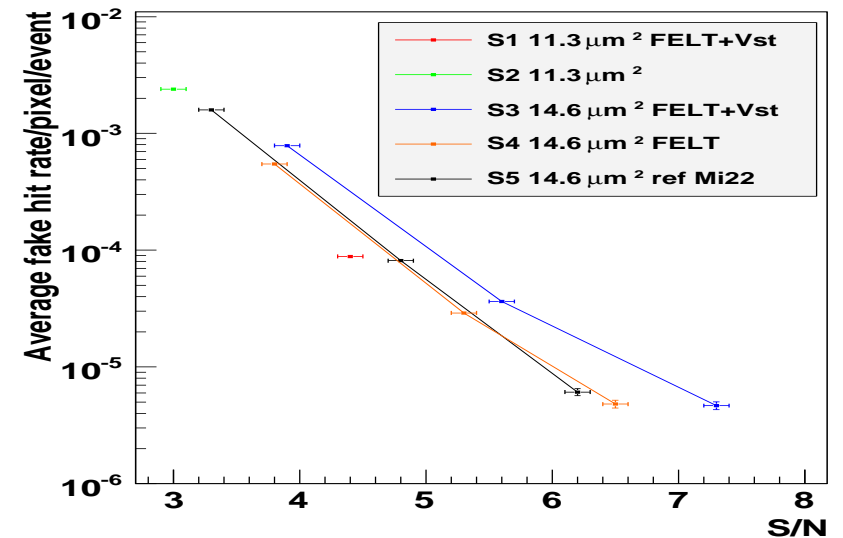
Det. eff. vs SNR before and after irradiation (150 kRad)

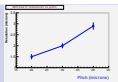
▶▶▶ Pixel & column parallel architecture  
with integrated discriminators  
**Fully Validated !!!**

M22bis digital Efficiency after 150kRad



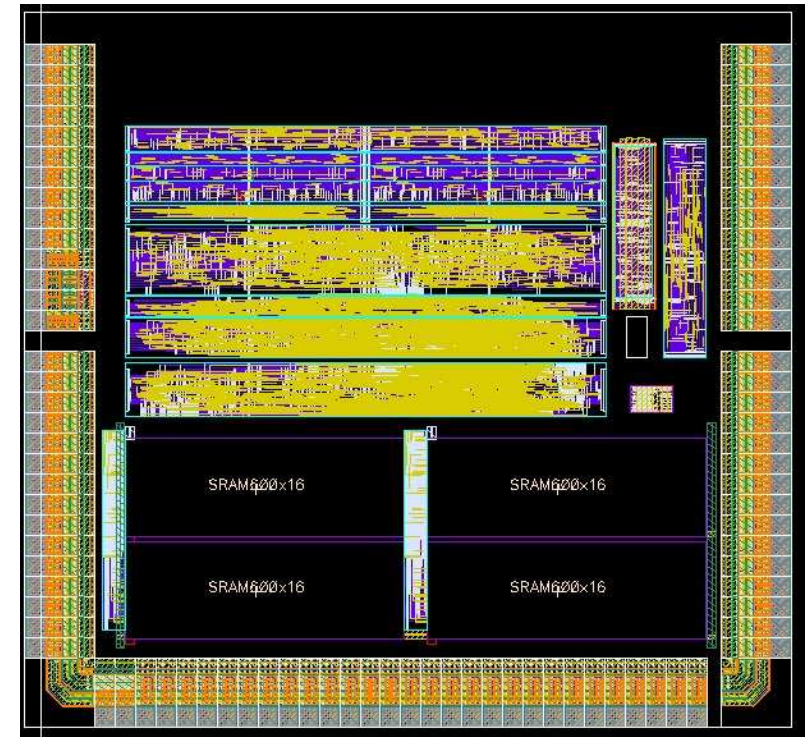
M22bis digital fake hit rate





■ 1st chip (SDC-2/SUZE-01) with integrated  $\emptyset$  and output memories (no pixels) :

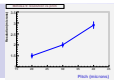
- ✧ 2 step, raw by raw, logic :
  - ◇ step-1 (inside blocks of 64 columns) :
    - identify up to 6 series of  $\leq 4$  neighbour pixels per raw
    - delivering signal  $>$  discriminator threshold
  - ◇ step-2 : read-out outcome of step-1 in all blocks
  - and keep up to 9 series of  $\leq 4$  neighbour pixels
- ✧ 4 output memories (512x16 bits) taken from AMS I.P. lib.
- ✧ surface  $\sim 3.9 \times 3.6 \text{ mm}^2$



■ Test results summary :

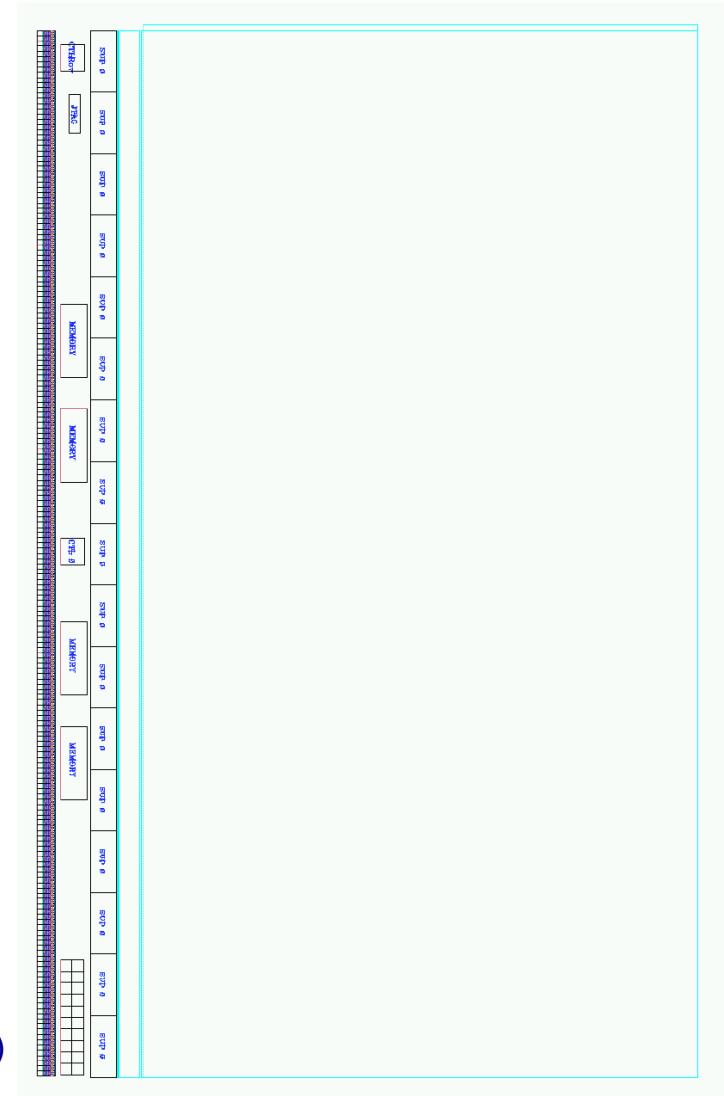
- ✧ back from foundry end of Sept. '07  $\rightarrow$  (lab) tests completed
- ✧ design performances reproduced up to  $1.15 \times$  design read-out frequency ( $T_{room}$ ) :
  - noise values as predicted, no pattern encoding error, can handle  $> 100$  hits/frame at rate  $> 10^4$  frames/s

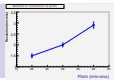
■ Still to do : evaluate radiation tolerance (latch-up) of output memories



## Autumn 2008 : fabrication of MIMOSA-26 = Final Sensor (TC )

- ✳ IDC/M-22 (binary outputs) complemented with  $\emptyset$  (SDC-2/SUZE-01)
- ✳ best performing (rad. tol. ) pixel architecture of IDC/M-22(bis)
  - ↪ wait for Octobre beam test final results
- ✳ Active surface : 1152 columns of 576 pixels (21.2 x 10.6 mm<sup>2</sup>)
  - ↪ extension of IDC & SDC-2 from 128 col. to 9 x 128 col.
- ✳ Pixel pitch : 18.4  $\mu m$   $\rightarrow$   $\sim$  0.7 million pixels
  - ↪  $\sigma_{sp} \gtrsim 3.5 \mu m \Rightarrow$  pointing resolution  $\sim 2 \mu m$  on DUT surface
- ✳ Integration time  $\sim 110 \mu s \rightarrow \sim 10^4$  frames / second
- ✳  $\emptyset$  based on 18 groups of 64 columns and assuming  $\leq 9$  "clusters" per row
- ✳ Chip dimensions :  $\sim 21 \times 12$  mm<sup>2</sup>
- ✳ Data throughput: 1 output at  $\geq 80$  Mbits/s or 2 outputs at  $\geq 40$  Mbits/s
- ✳ Engineering run : 2 (+  $\leq 4$ ) wafers of  $\gtrsim 30$  chips expected (if yield  $\sim 50$  % )
- ✳ Design under way  $\Rightarrow$  planned submission date  $\geq$  mid-November '08





- Col. // architecture with discri. outputs validated for m.i.p. detection on real scale (128 col. of final length) :
  - ⇒ read-out frequency  $\sim 10^4$  frames/s ✓
  - ⇒ pixel noise  $\sim 10\text{--}13 e^- ENC \Rightarrow S/N \sim 17\text{--}22$  (MPV) ✓
  - ⇒  $\epsilon_{det} > 99.5\%$  with fake rate  $\sim O(10^{-4} - 10^{-5})$ , similar to MIMOSA-16 ✓
  - ⇒  $\sigma_{sp} \gtrsim 3.5 \mu m \Rightarrow$  resolution on impact position on DUT surface  $\lesssim 2 \mu m$  ✓
  
- $\emptyset$   $\mu$ -circuit with output buffers validated for 128 col. at read-out frequency  $>$  nominal value ✓
  
- Radiation tolerance :
  - ⇒ achieved ionising radiation tolerance of pixel array sufficient for use of BT at CERN, FermiLab, ... ✓  
(source of noise increase still being investigated)
  - ⇒ under way : non-ionising radiation tolerance assessment and latch-up tests of output memories
  
- ⇒ TC  $\equiv$  final sensor (combining col. // architecture with  $\emptyset$   $\mu$ -circuit) :
  - ⇒ design under way (crucial issues : extension from 128 to 1152 col. of IDC combined with SDC-2)
  - ⇒ in absence of unexpected pb, submission will occur  $\gtrsim$  mid-Novembre '08
  - ↪ TC sensor tests expected to start in January 2009